

FLL410IK-3C

L-Band High Power GaAs FET

FEATURES

- High Output Power: Pout=46.0dBm(Typ.)
- High Gain: GL=13.0dB(Typ.)
- High PAE: η_{add} =52%(Typ.)
- Broad Band: 2.5~2.7GHz
- Hermetically Sealed Package

DESCRIPTION

The FLL410IK-3C is a partially matched 40 Watt GaAs FET that is designed for use in 2.5 – 2.7 GHz band amplifiers. This new product is uniquely suited for use in MMDS applications as it offers excellent linearity, high efficiency, high gain, long term reliability and ease of use.



Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATINGS (Case Temperature Tc=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	15	V
Gate-Source Voltage	V _{GS}	-5	V
Total Power Dissipation	PT	100	W
Storage Temperature	T _{stg}	-65 to +175	°C
Channel Temperature	T _{ch}	175	°C

RECOMMENDED OPERATING CONDITION(Case Temperature Tc=25°C)

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	V _{DS}		≤12	V
Gate Current	I _{GF}	R _G =5Ω	≤88	mA
Gate Current	I _{GR}	R _G =5Ω	≥-25	mA
Operating Channel Temperature	T _{ch}		≤145	°C

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25°C)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Drain Current	I _{DSS}	V _{DS} =5V, V _{GS} =0V	-	4.0	-	A
Pinch-off Voltage	V _p	V _{DS} =5V, I _{DSS} =110mA	-0.1	-0.3	-0.5	V
Gate-Source Breakdown Voltage	V _{GSO}	I _{GS} =-1.1mA	-5.0	-	-	V
Output Power	P _{OUT}	V _{DS} =12V f=2.6 GHz I _{DSS} =3A Pin=35.0dBm	45.0	46.0	-	dBm
Linear Gain *1	GL		12.0	13.0	-	dB
Drain Current	I _{DSR}		-	5.9	7.6	A
Power-added Efficiency	η_{add}		-	52	-	%
Thermal Resistance	R _{th}	Channel to Case	-	1.3	1.5	°C/W

* 1 : GL is measured at Pin=22.0dBm

CASE STYLE: IK

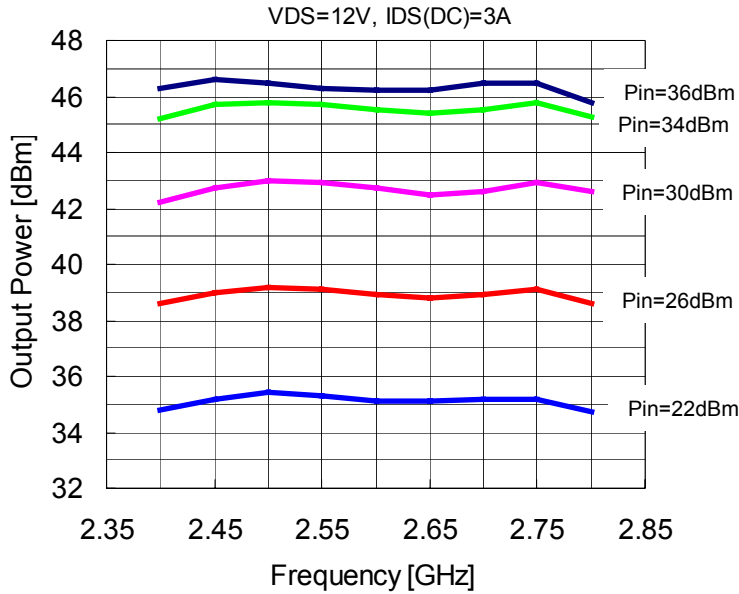
ESD	Class III	2000V ~
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Note : Based on EIAJ ED-4701 C-111A(C=100pF, R=1.5kΩ)

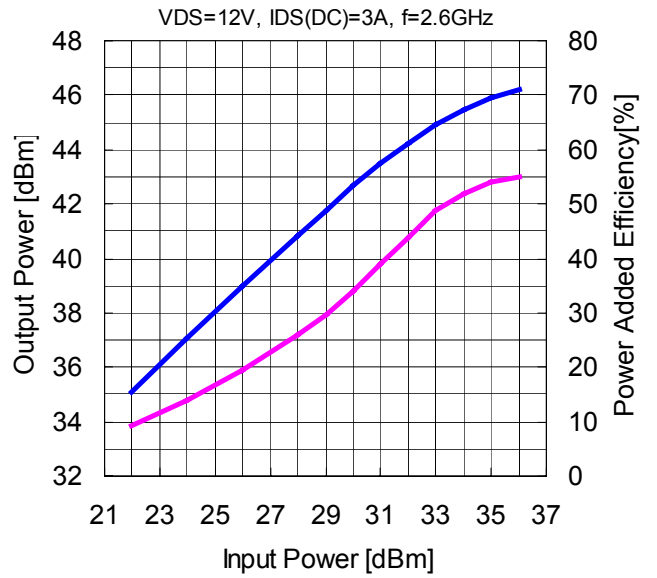
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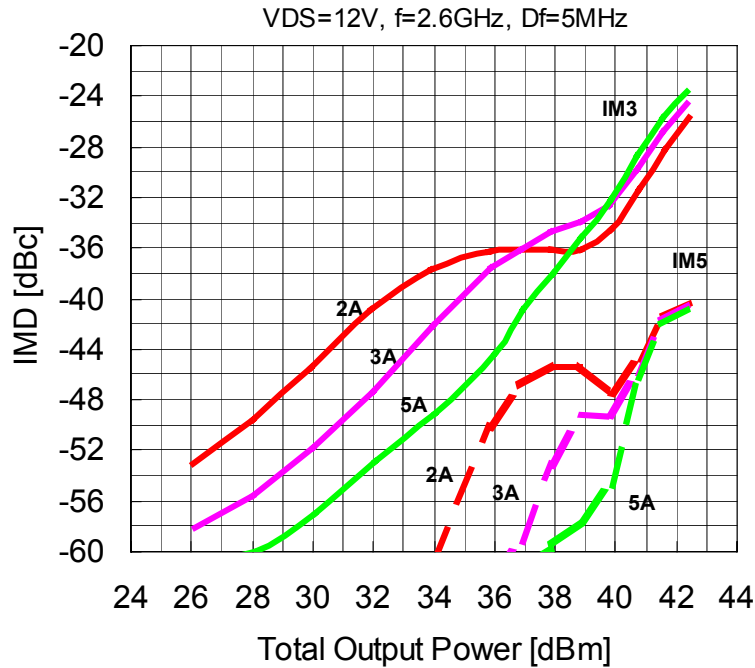
OUTPUT POWER vs. INPUT POWER



OUTPUT POWER , POWER ADDED EFFICIENCY vs. TOTAL INPUT POWER



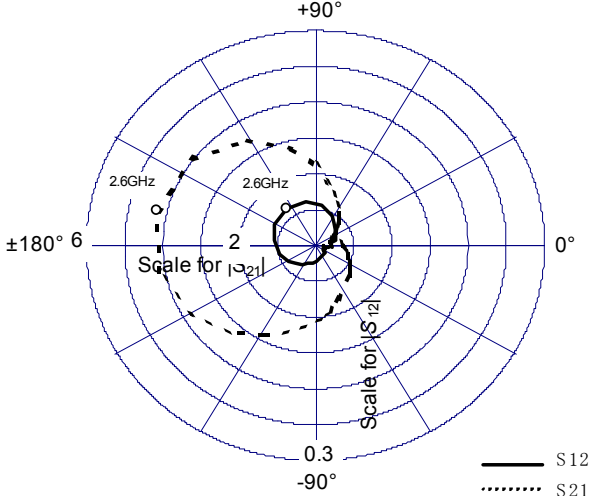
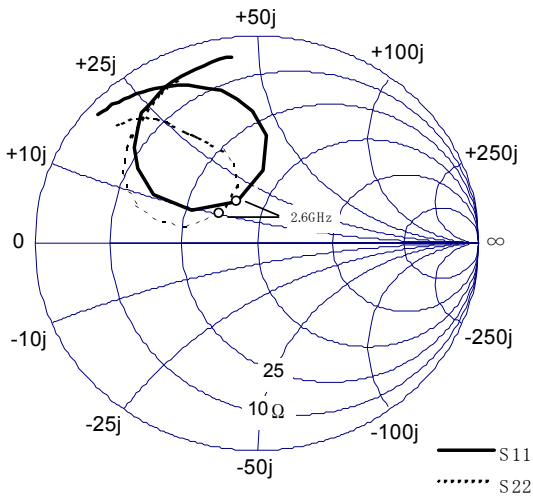
IMD vs. TOTAL OUTPUT POWER



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■ S-PARAMETER



VDS=12V, IDS=3.0A

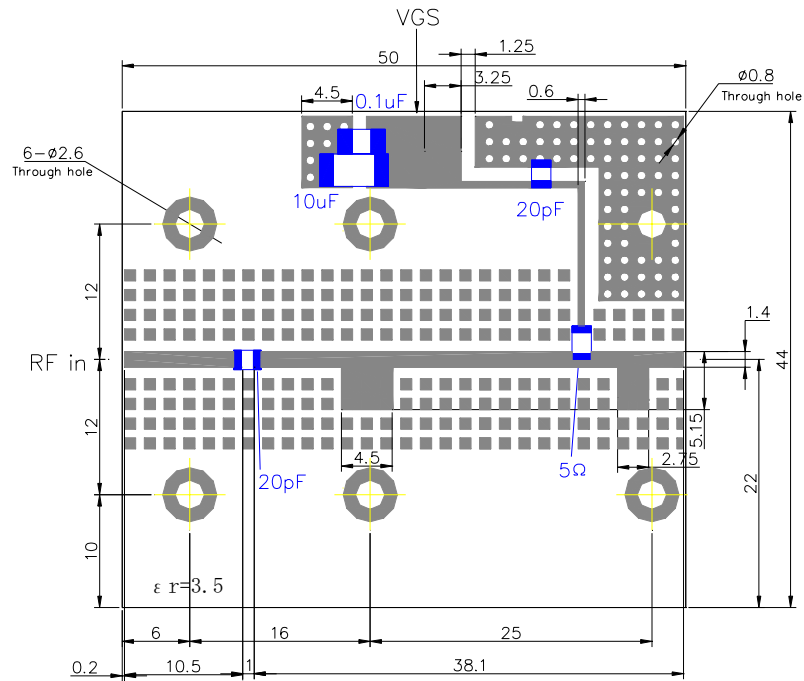
Freq [GHz]	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.50	0.95	139.13	0.66	5.71	0.01	-7.76	0.85	137.80
1.60	0.94	136.13	0.73	-1.34	0.01	-21.24	0.83	134.28
1.70	0.92	132.48	0.83	-11.38	0.01	-27.54	0.80	130.79
1.80	0.91	129.08	0.93	-21.69	0.01	-37.64	0.76	127.82
1.90	0.89	125.19	1.08	-33.36	0.01	-48.85	0.72	125.28
2.00	0.87	121.65	1.26	-45.28	0.01	-64.79	0.68	122.79
2.20	0.83	112.20	1.82	-76.40	0.02	-97.72	0.61	119.58
2.30	0.78	106.32	2.27	-95.83	0.02	-122.75	0.57	117.16
2.40	0.70	97.54	2.86	-118.23	0.03	-148.63	0.52	112.58
2.50	0.52	85.55	3.75	-149.12	0.04	173.08	0.40	105.59
2.60	0.22	114.34	4.29	166.53	0.04	127.14	0.22	139.17
2.70	0.52	153.17	3.43	121.10	0.04	82.29	0.47	165.62
2.80	0.72	139.88	2.23	89.90	0.03	50.87	0.65	155.17
2.90	0.82	129.39	1.54	71.09	0.02	27.82	0.72	145.97
3.00	0.85	121.63	1.10	57.03	0.02	15.34	0.76	138.08
3.10	0.87	116.02	0.87	45.39	0.01	-3.89	0.79	130.98
3.20	0.88	110.41	0.66	35.06	0.01	-7.86	0.82	125.09
3.30	0.89	105.71	0.56	28.49	0.01	-16.93	0.84	120.80
3.40	0.90	100.75	0.47	20.22	0.01	-25.52	0.86	117.16
3.50	0.91	97.00	0.42	15.07	0.01	-22.89	0.86	113.34

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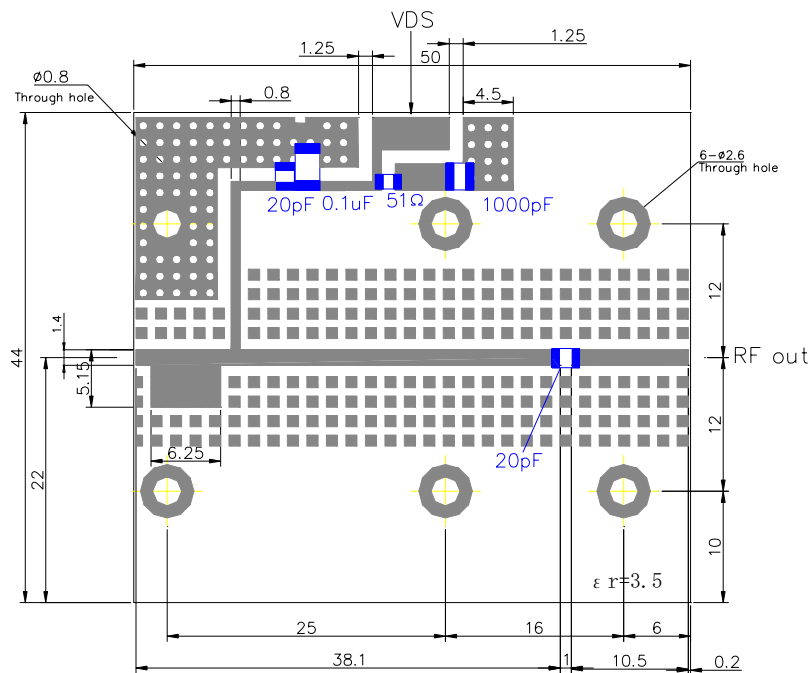
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■ BOARD LAYOUT(Reference)

<INPUT SIDE>



<OUTPUT SIDE>

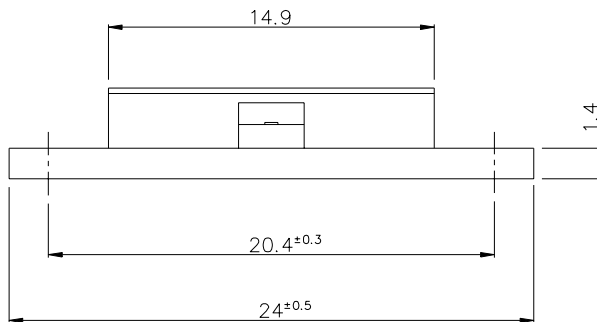
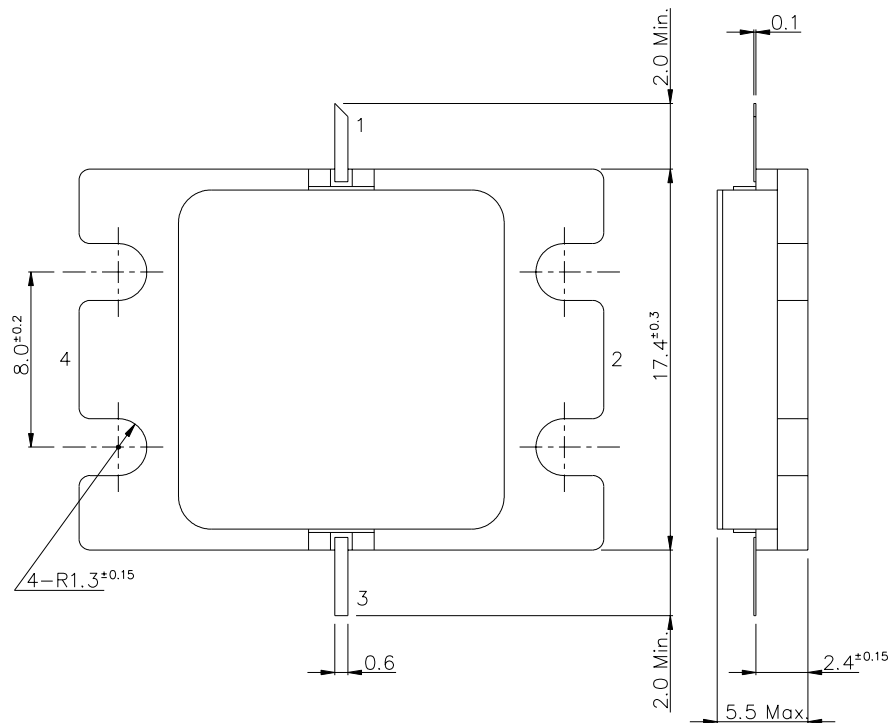


$\epsilon_r=3.5$, $t=0.6\text{mm}$
Unit : mm

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■ Package Out Line



PIN ASSIGNMENT

- 1 : GATE
- 2 : SOURCE
- 3 : DRAIN
- 4 : SOURCE

Unit : mm

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For further information please contact :

FUJITSU COMPOUND SEMICONDUCTOR, INC.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
TEL: (408) 232-9500
FAX: (408) 428-9111
www.fcsi.fujitsu.com

FUJITSU QUANTUM DEVICES EUROPE LTD.

Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
TEL: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

FUJITSU QUANTUM DEVICES SINGAPORE PTE LTD.

HONG KONG BRANCH
Rm. 1101, Ocean Centre, 5 Canton Rd.
Tsim Sha Tsui, Kowloon, Hong Kong
TEL: +852-2377-0227
FAX: +852-2377-3921

FUJITSU QUANTUM DEVICES LTD.

1000 Kamisukiahara, showa-cho
Nakakomagun, Yamanashi
409-3883, Japan
(Kokubo Industrial Park)
TEL: +81-55-275-4411
FAX: +81-55-275-9461

FUJITSU QUANTUM DEVICES LIMITED

Business Development Division
Hachioji Daiichi-Seimei Bldg., 11th Floor
3-20-6 Myojin-cho
Hachioji-city, Tokyo 192-0046, Japan
TEL: +81-426-43-5885
FAX: +81-426-43-5582

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- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.